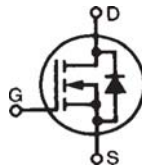


High Voltage Power MOSFET

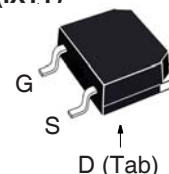
IXTT1N450HV IXTH1N450HV

$V_{DSS} = 4500V$
 $I_{D25} = 1A$
 $R_{DS(on)} \leq 80\Omega$

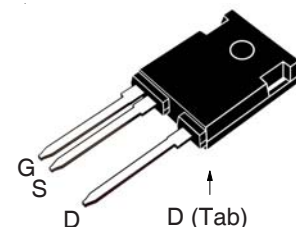
N-Channel Enhancement Mode



TO-268HV (IXTT)



TO-247HV (IXTH)



G = Gate D = Drain
 S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	4500	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$	4500	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ C$	1	A
I_{DM}	$T_C = 25^\circ C$, Pulse Width Limited by T_{JM}	3	A
P_D	$T_C = 25^\circ C$	520	W
T_J		- 55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		- 55 ... +150	$^\circ C$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ C$
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
F_C	Mounting Force (TO-263HV)	10..65 / 22..14.6	N/lb
M_d	Mounting Torque (TO-247HV)	1.13/10	Nm/lb.in
Weight	TO-263HV	2.5	g
	TO-247HV	6.0	g

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	3.5		6.0 V
I_{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = 3.6kV$, $V_{GS} = 0V$ $V_{DS} = 4.5kV$ $V_{DS} = 3.6kV$ $T_J = 100^\circ C$			5 μA
				25 μA
				15 μA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 50mA$, Note 1			80 Ω

Features

- High Blocking Voltage
- High Voltage Package

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- High Voltage Power Supplies
- Capacitor Discharge Applications
- Pulse Circuits
- Laser and X-Ray Generation Systems

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 50\text{V}$, $I_D = 200\text{mA}$, Note 1	0.40	0.70	S
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		1700	pF
C_{oss}			80	pF
C_{rss}			29	pF
R_{Gi}	Gate Input Resistance		12	Ω
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 500\text{V}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 10\Omega$ (External)		30	ns
t_r			43	ns
$t_{d(off)}$			73	ns
t_f			120	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 1\text{kV}$, $I_D = 0.5 \cdot I_{D25}$		46	nC
Q_{gs}			8	nC
Q_{gd}			23	nC
R_{thJC}	TO-247HV			0.24 $^\circ\text{C/W}$
R_{thCS}			0.21	$^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			1 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			5 A
V_{SD}	$I_F = 1\text{A}$, $V_{GS} = 0\text{V}$, Note 1			2.0 V
t_{rr}	$I_F = 1\text{A}$, $-di/dt = 50\text{A}/\mu\text{s}$, $V_R = 100\text{V}$		1.75	μs

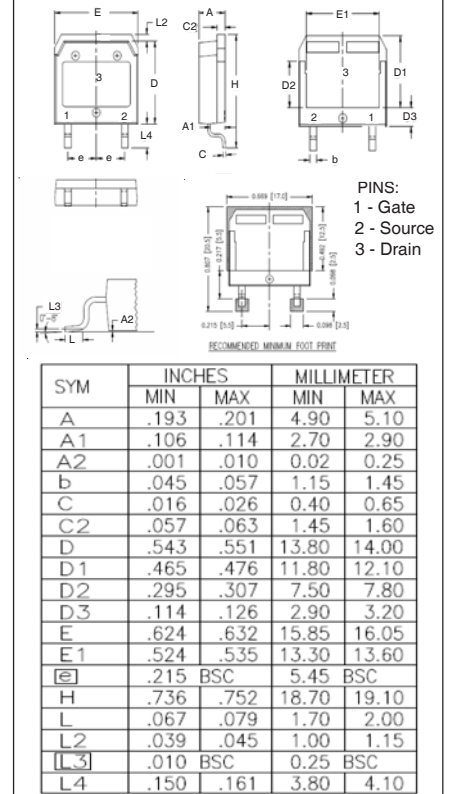
Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

TO-268HV Outline



TO-247HV Outline

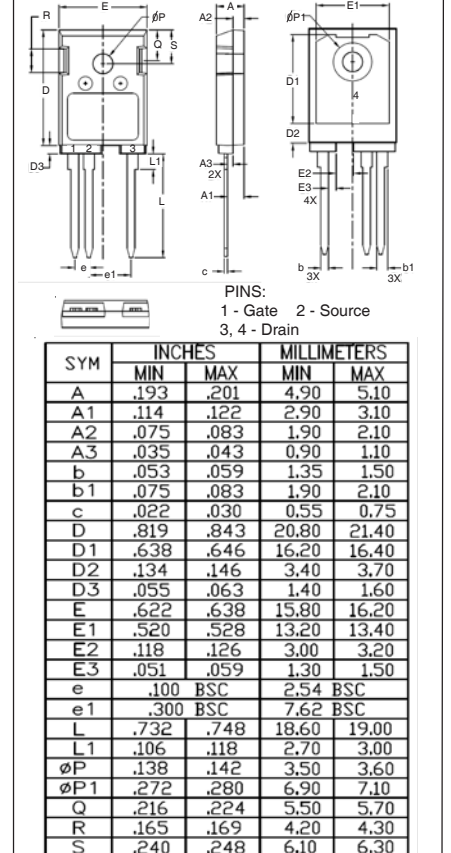


Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

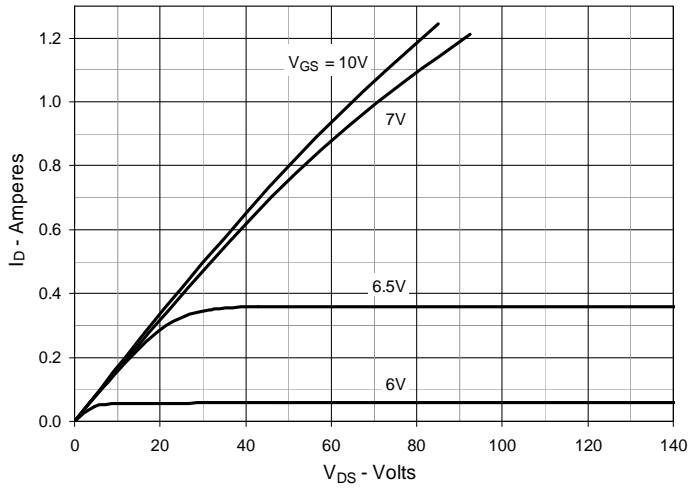


Fig. 2. Output Characteristics @ $T_J = 125^\circ\text{C}$

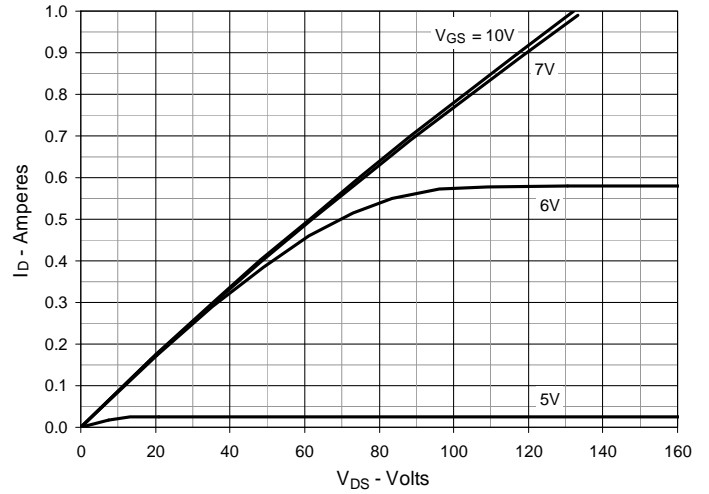


Fig. 3. $R_{DS(on)}$ Normalized to $I_D = 0.5\text{A}$ Value vs. Junction Temperature

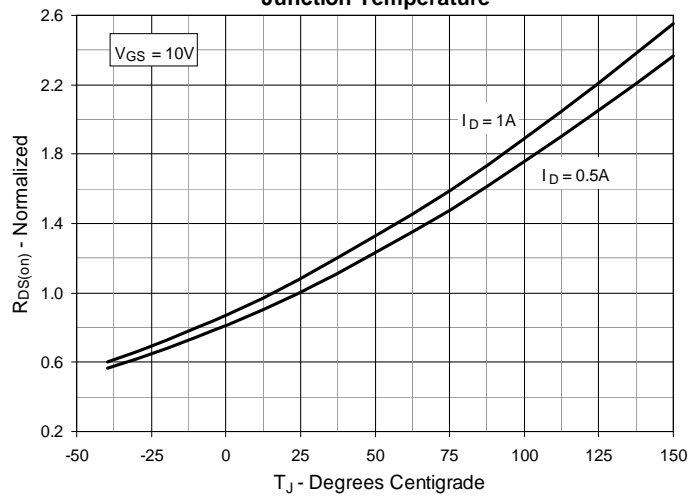


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 0.5\text{A}$ Value vs. Drain Current

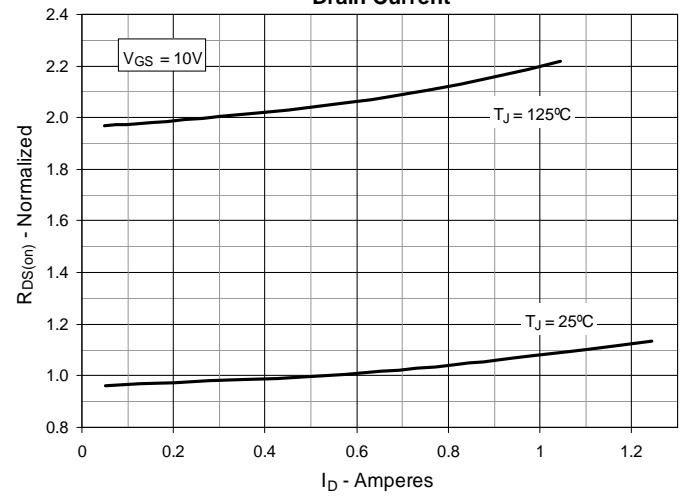


Fig. 5. Maximum Drain Current vs. Case Temperature

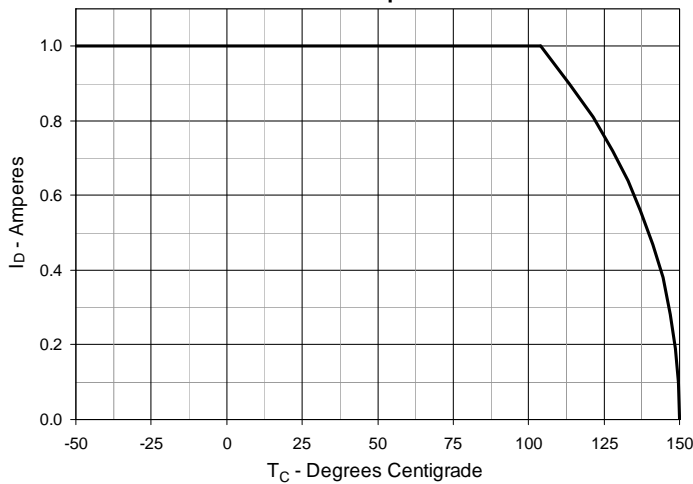


Fig. 6. Input Admittance

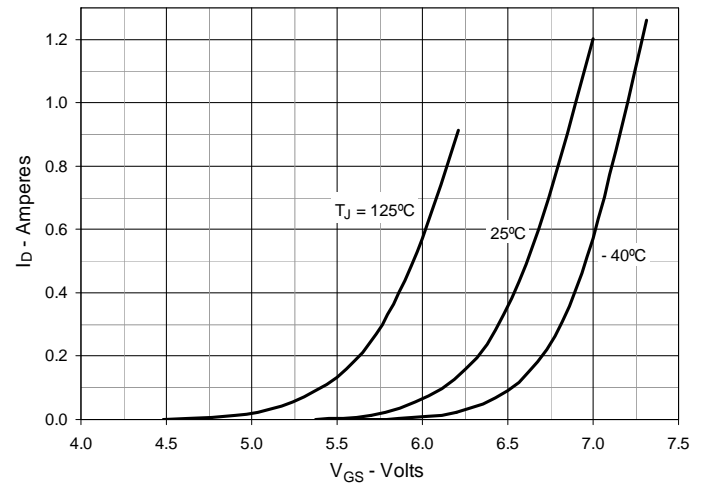


Fig. 7. Transconductance

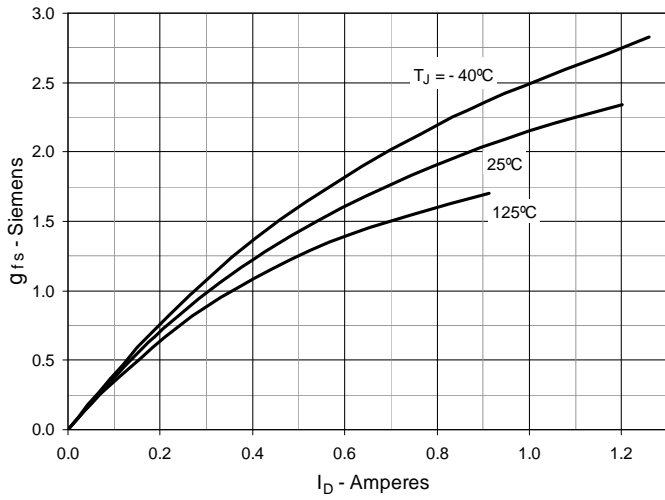


Fig. 8. Forward Voltage Drop of Intrinsic Diode

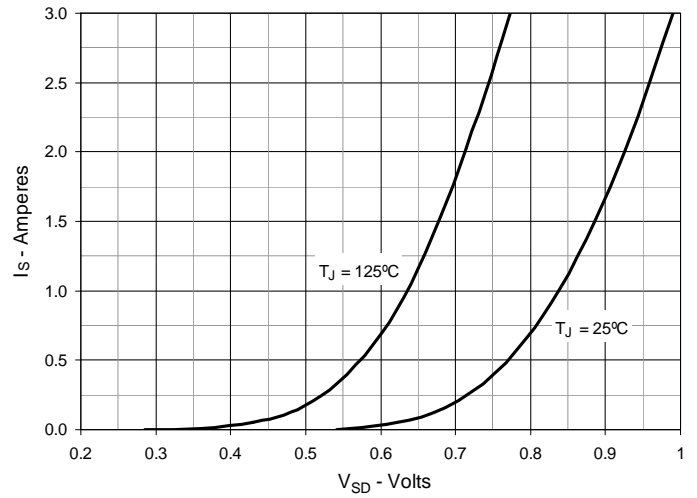


Fig. 9. Gate Charge

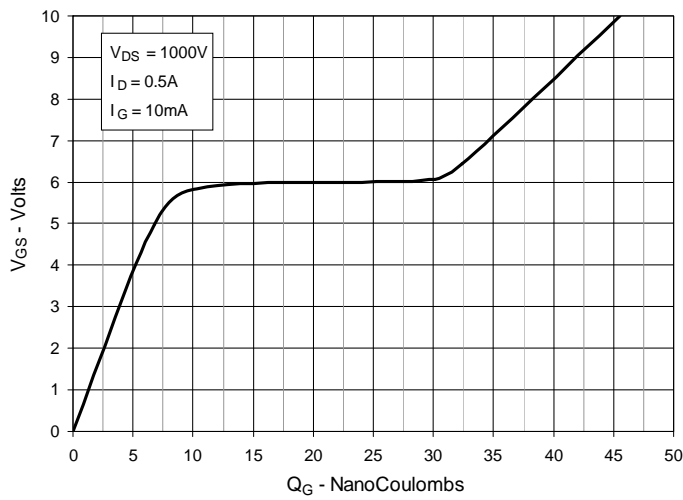


Fig. 10. Capacitance

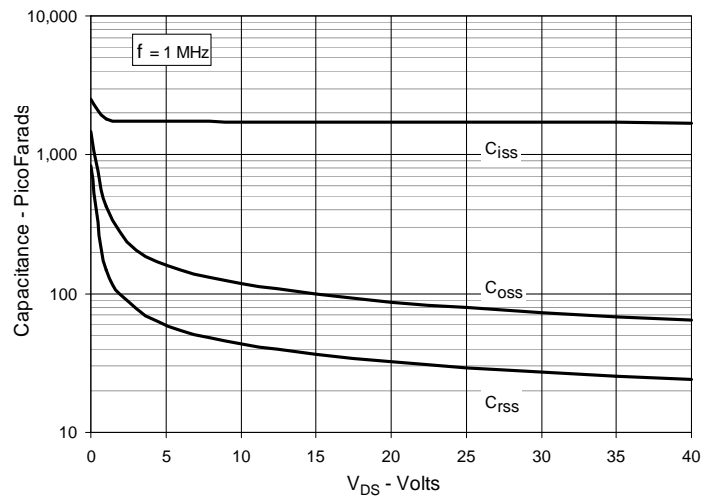
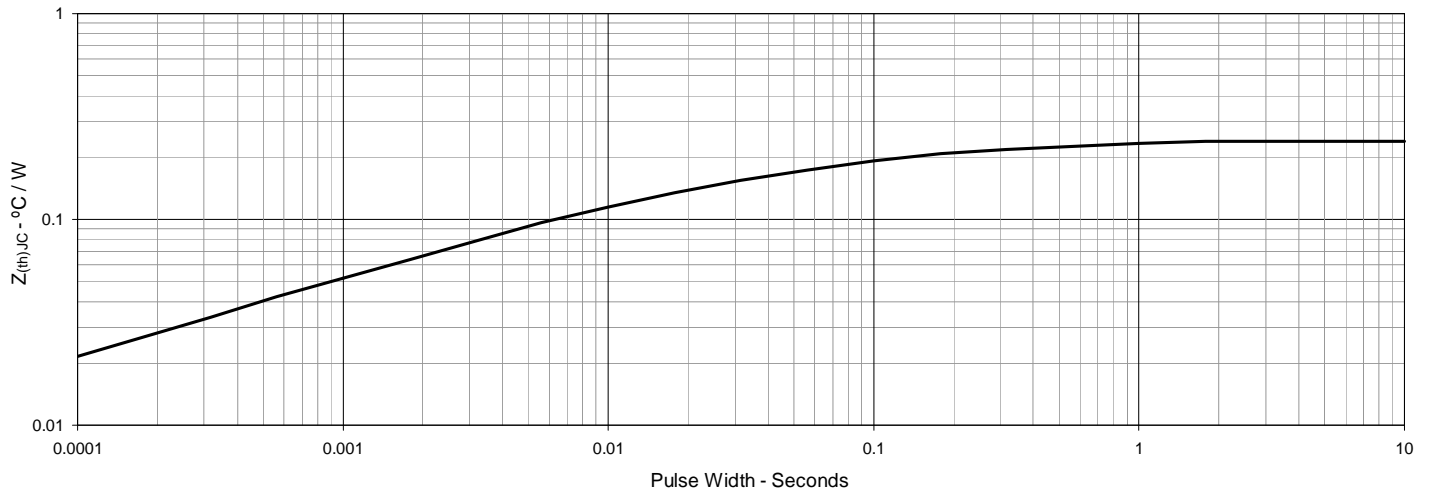
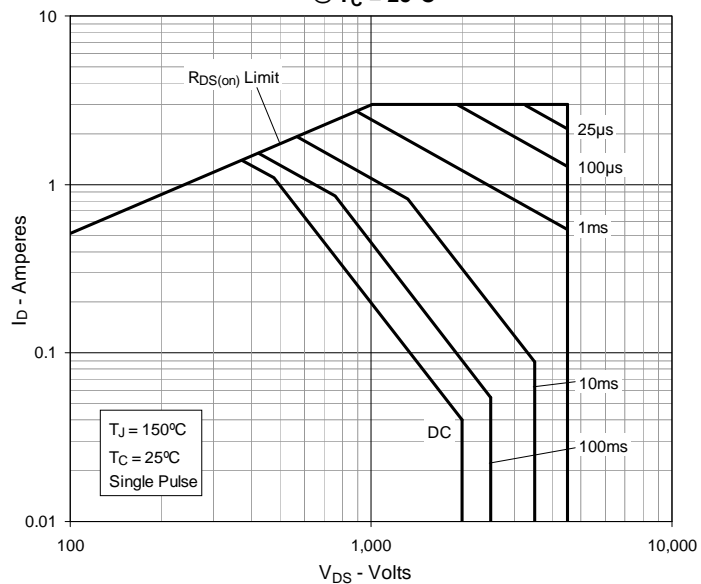


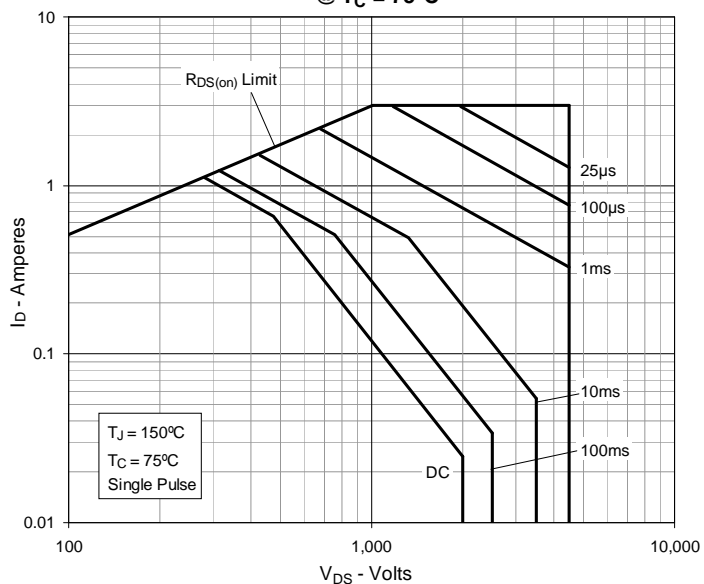
Fig. 11. Maximum Transient Thermal Impedance



**Fig. 12. Forward-Bias Safe Operating Area
@ $T_C = 25^\circ\text{C}$**



**Fig. 13. Forward-Bias Safe Operating Area
@ $T_C = 75^\circ\text{C}$**





Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.